

N-channel LFPAK 100V 27.5 mΩ standard level MOSFET

Rev. 02 — 30 March 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

1.4 Quick reference data

Table 1. Quick reference

- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

Table 1.	Quick reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	42	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	89	W
Tj	junction temperature		-55	-	175	°C
Avalance	ne ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	68	mJ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A};$	-	10.3	-	nC
Q _{G(tot)}	total gate charge	$V_{DS} = 50 \text{ V}; \text{ see } \frac{\text{Figure } 15}{\text{and } \frac{16}{2}}$	-	33	-	nC

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Table 1.	Quick reference	.continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static c	haracteristics					
R_{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A}; \\ T_{j} = 100 \text{ °C}; \text{ see } \overline{Figure \ 13} \end{array}$	-	-	52	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \underline{\text{Figure } 14} \end{array}$	-	21.4	27.5	mΩ

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source	mb	
3	S	source		
4	G	gate	Q	
mb	D	mounting base; connected to drain		mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PSMN028-100Y	S LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669	

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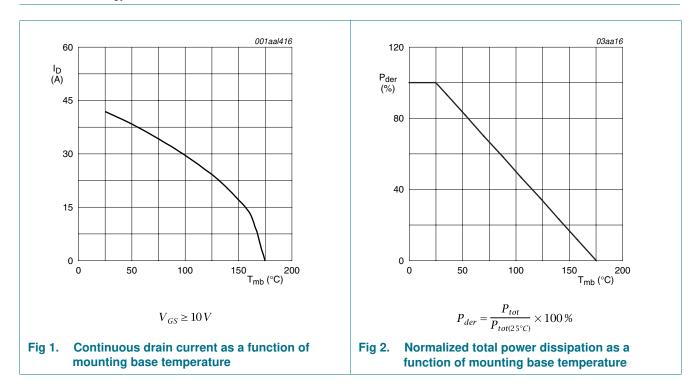
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4. Limiting values

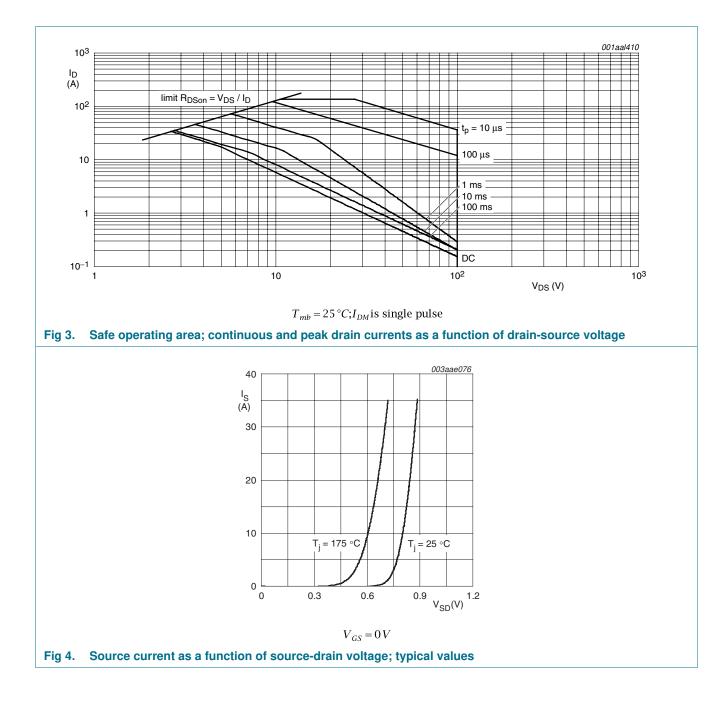
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
-			101111		
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	T _j ≤ 175 °C; T _j ≥ 25 °C; R _{GS} = 20 kΩ	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	30	А
		$V_{GS} = 10 \text{ V}; \text{ T}_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{1}$	-	42	А
I _{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	137	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	89	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-dr	ain diode				
I _S	source current	T _{mb} = 25 °C; see <u>Figure 4</u>	-	42	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	137	А
Avalanche	e ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_{D} = 34 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω	-	68	mJ



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5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	0.81	1.68	K/W
1					001aal406	

Table 5. Thermal characteristics

1	001aal406
$-\delta = 0.5$	
Z _{th(j-mb)} (K/W)	
(K [*] W)	
0.2	
0.05	
single shot	
10^{-2} 10^{-6} 10^{-5} 10^{-4} 10^{-3} 10^{-2}	
10^{-6} 10^{-5} 10^{-4} 10^{-3} 10^{-2}	10^{-1} 1
	t _p (s)

Fig 5. Transient termal impedance from junction to mounting base as a function of pulse duration

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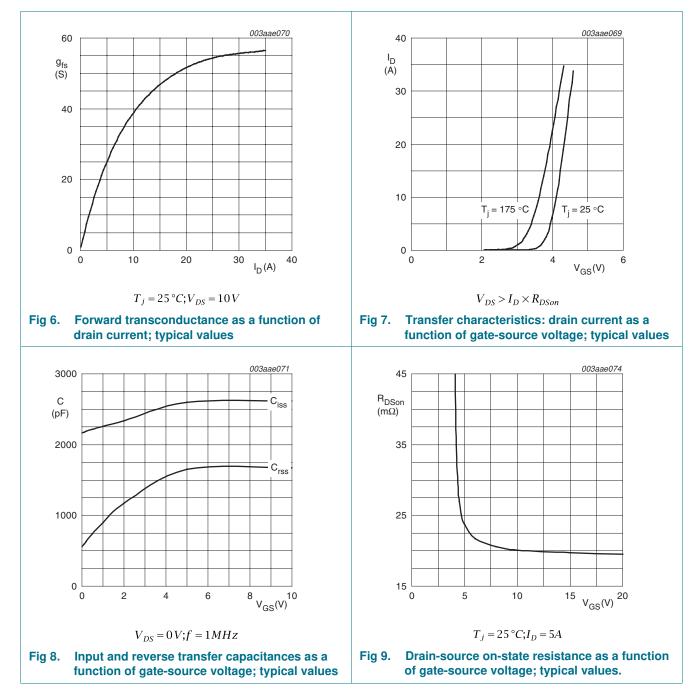
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; \text{see } \frac{\text{Figure } 11}{1000}$	1	-	-	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; \text{see } \frac{\text{Figure } 12}{\text{and } \frac{11}{2}}$	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; \text{see } \underline{Figure 11}$	-	-	4.7	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C	-	-	50	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	2	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 13</u>	-	-	52	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 13</u>	-	49.9	74.3	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see <u>Figure 14</u>	-	21.4	27.5	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.5	1.5	Ω
Dynamic	characteristics					
$Q_{G(tot)}$ total gate charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see Figure 15 and $\underline{16}$	-	33	-	nC	
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	25	-	nC
Q _{GS}	gate-source charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see Figure 15 and $\underline{16}$	-	7.2	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 15</u>	-	5	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.2	-	nC
Q _{GD}	gate-drain charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 15</u> and <u>16</u>	-	10.3	-	nC
V _{GS(pl)}	gate-source plateau voltage	$V_{DS} = 50 \text{ V}$; see <u>Figure 15</u> and <u>16</u>	-	4.1	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C;	-	1634	-	pF
C _{oss}	output capacitance	see Figure 17	-	132	-	pF
C _{rss}	reverse transfer capacitance		-	85	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 3.3 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	15	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; T_j = 25 \ ^{\circ}C$	-	14	-	ns
t _{d(off)}	turn-off delay time		-	33	-	ns
t _f	fall time		_	12	-	ns

Source-drain diode

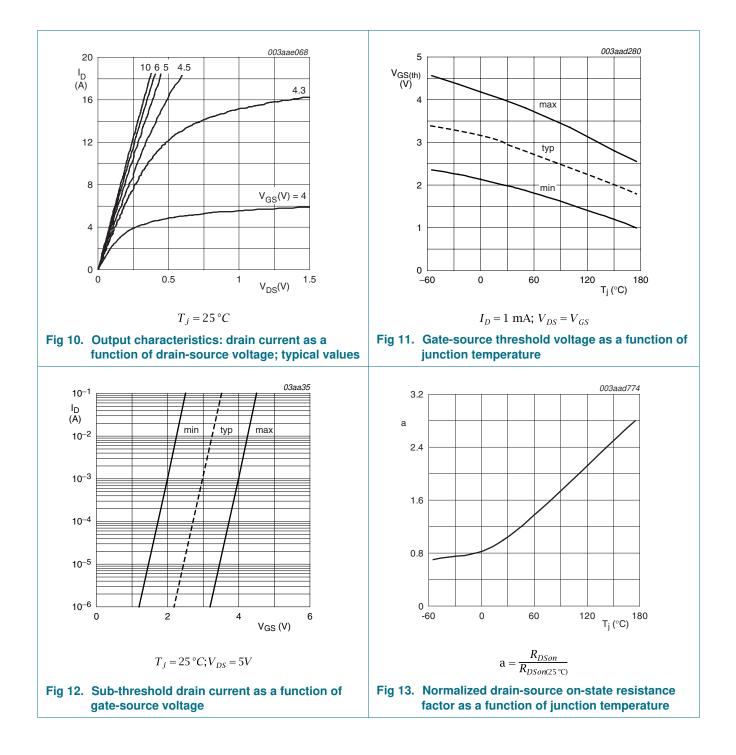
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Table 6.	Characteristics continued						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; \text{see } \frac{\text{Figure 4}}{1000 \text{ C}}$	-	0.8	1.2	V	
t _{rr}	reverse recovery time	$I_{S} = 5 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	48.7	-	ns	
Qr	recovered charge	$V_{DS} = 50 V$	- 95.7		-	nC	

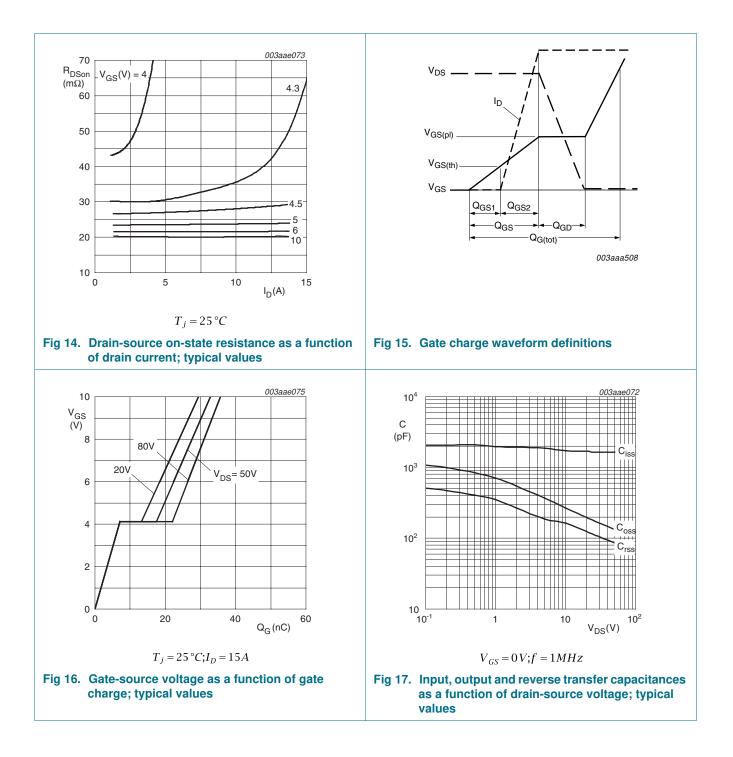


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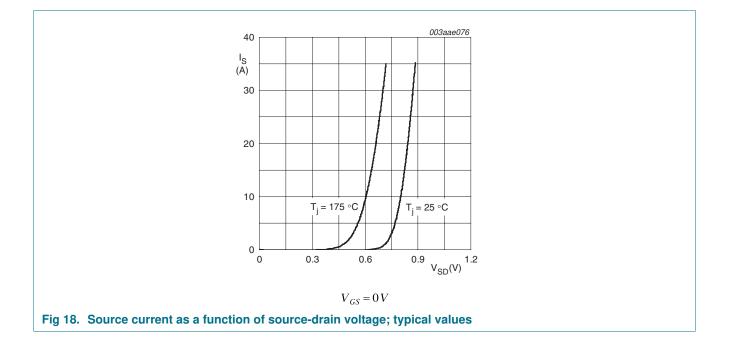
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7. Package outline

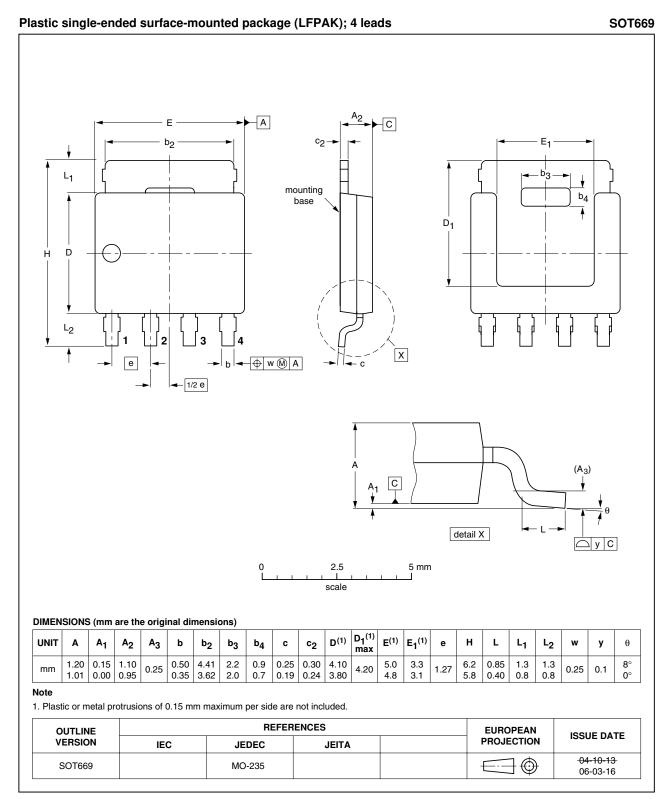


Fig 19. Package outline SOT669 (LFPAK)

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8. Revision history

Table 7. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN028-100YS_2	20100330	Product data sheet	-	PSMN028-100YS_1
Modifications:	 Status chail 	nged from objective to pr	oduct.	
	 Various cha 	anges to content.		
PSMN028-100YS_1	20100210	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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